

**Amendments to the Claims:**

Claim 1 has been amended herein. Please note that all claims currently pending and under consideration in the referenced application are shown below. Please enter these claims as amended. This listing of claims will replace all prior versions and listings of claims in the application.

**Listing of Claims:**

Please cancel claims 19, 20 and 26 through 29 without prejudice or disclaimer.

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1. (Currently amended) A method of forming a semiconductor device, comprising:  
providing a semiconductor substrate having an active surface including at least one layer of integrated circuitry thereon, said active surface defining a plurality of individual die locations thereon, and a plurality of bond pads associated with each of said plurality of individual die locations;  
forming at least one intermediate conductive element on at least one bond pad of said plurality of bond pads;  
forming a pattern of mutually transverse channels in said active surface to a depth below said at least one layer of integrated circuitry, said channels circumscribing a semiconductor element location comprised of at least one individual die and exposing peripheral edges of said at least one layer of integrated circuitry; and  
forming a layer of encapsulant material over substantially all of said active surface and into said channels such that a surface of said layer of encapsulant material has a pattern of depressions over said channels and a portion of said at least one intermediate conductive element is exposed through and coplanar with said surface of said layer of ~~encapsulant~~ encapsulant material.